Sheikh Ziaur Rahaman

List of Publications by Year
in descending order

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28	664	567281 15	580821 25
papers	citations	h-index	g-index

28	28	28	922
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	An 8kb spin-orbit-torque magnetic random-access memory. , 2021, , .		6
2	Size-Dependent Switching Properties of Spin-Orbit Torque MRAM With Manufacturing-Friendly 8-Inch Wafer-Level Uniformity. IEEE Journal of the Electron Devices Society, 2020, 8, 163-169.	2.1	12
3	Pulse-Width and Temperature Effect on the Switching Behavior of an Etch-Stop-on-MgO-Barrier Spin-Orbit Torque MRAM Cell. IEEE Electron Device Letters, 2018, 39, 1306-1309.	3.9	29
4	The Role of Ti Buffer Layer Thickness on the Resistive Switching Properties of Hafnium Oxide-Based Resistive Switching Memories. Langmuir, 2017, 33, 4654-4665.	3.5	51
5	Understanding of multi-level resistive switching mechanism in GeOx through redox reaction in H2O2/sarcosine prostate cancer biomarker detection. Scientific Reports, 2017, 7, 11240.	3.3	27
6	Scalability and reliability issues of Ti/HfOx-based 1T1R bipolar RRAM: Occurrence, mitigation, and solution. Applied Physics Letters, 2017, 110, .	3.3	19
7	Occurrence and solution to overcome 1stRESET resistance pinning effect in Ti/HfO<inf>x</inf> based RRAM for low power nonvolatile memory applications. , 2017, , .		0
8	Retention Model of TaO/HfO x and TaO/AlO x RRAM with Self-Rectifying Switch Characteristics. Nanoscale Research Letters, 2017, 12, 407.	5.7	16
9	Effect of Ti buffer layer on HfOx-based bipolar and complementary resistive switching for future memory applications. , 2016, , .		1
10	Temperature-Dependent Non-linear Resistive Switching Characteristics and Mechanism Using a New W/WO3/WOx/W Structure. Nanoscale Research Letters, 2016, 11, 389.	5.7	43
11	Resistive and New Optical Switching Memory Characteristics Using Thermally Grown Ge0.2Se0.8 Film in Cu/GeSex/W Structure. Nanoscale Research Letters, 2015, 10, 392.	5.7	10
12	Conductive-bridging random access memory: challenges and opportunity for 3D architecture. Nanoscale Research Letters, 2015, 10, 188.	5.7	76
13	Resistive switching memory characteristics of Ge/GeO x nanowires and evidence of oxygen ion migration. Nanoscale Research Letters, 2013, 8, 220.	5.7	40
14	Comparison of resistive switching characteristics using copper and aluminum electrodes on GeOx/W cross-point memories. Nanoscale Research Letters, 2013, 8, 509.	5.7	10
15	Ti/HfO2 Based RRAM Operation Voltage Scaling for Embedded Memory. ECS Transactions, 2013, 52, 39-44.	0.5	1
16	Bipolar Resistive Switching Memory Characteristics Using Al/Cu/GeO_x/W Memristor. ECS Transactions, 2012, 45, 257-261.	0.5	15
17	Record Resistance Ratio and Bipolar/Unipolar Resistive Switching Characteristics of Memory Device Using Germanium Oxide Solid Electrolyte. Japanese Journal of Applied Physics, 2012, 51, 04DD11.	1.5	7
18	Excellent Uniformity and Multilevel Operation in Formation-Free Low Power Resistive Switching Memory Using IrO$_{x}$/AlO$_{x}$/W Cross-Point. Japanese Journal of Applied Physics, 2012, 51, 04DD10.	1.5	9

#	Article	IF	Citations
19	Excellent resistive memory characteristics and switching mechanism using a Ti nanolayer at the Cu/TaOx interface. Nanoscale Research Letters, 2012, 7, 345.	5.7	78
20	Enhanced nanoscale resistive switching memory characteristics and switching mechanism using high-Ge-content Ge0.5Se0.5 solid electrolyte. Nanoscale Research Letters, 2012, 7, 614.	5.7	29
21	Excellent Uniformity and Multilevel Operation in Formation-Free Low Power Resistive Switching Memory Using IrO_x/AlO_x/W Cross-Point. Japanese Journal of Applied Physics, 2012, 51, 04DD10.	1.5	16
22	Record Resistance Ratio and Bipolar/Unipolar Resistive Switching Characteristics of Memory Device Using Germanium Oxide Solid Electrolyte. Japanese Journal of Applied Physics, 2012, 51, 04DD11.	1.5	3
23	High-Î¤ Al₂O₃/WO_x Bilayer Dielectrics for Low-Power Resistive Switching Memory Applications. Japanese Journal of Applied Physics, 2011, 50, 10PH01.	1.5	21
24	Improved Resistive Switching Memory Characteristics Using Core-Shell IrO_xNano-Dots in Al₂O₃/WO_xBilayer Structure. Journal of the Electrochemical Society, 2011, 159, H177-H182.	2.9	34
25	High-Î¤ Al₂O₃/WO_xBilayer Dielectrics for Low-Power Resistive Switching Memory Applications. Japanese Journal of Applied Physics, 2011, 50, 10PH01.	1.5	13
26	Low power resistive switching memory using Cu metallic filament in Ge0.2Se0.8 solid-electrolyte. Microelectronics Reliability, 2010, 50, 643-646.	1.7	12
27	Bipolar Resistive Switching Memory Using Cu Metallic Filament in Ge[sub 0.4]Se[sub 0.6] Solid Electrolyte. Electrochemical and Solid-State Letters, 2010, 13, H159.	2.2	57
28	Nanoscale (EOT = 5.6 nm) nonvolatile memory characteristics using n-Si/SiO₂/HfAlO nanocrystal/Al₂O₃/Ptcapacitors. Nanotechnology, 2008, 19, 435202.	2.6	29